WHAT IS CLAIMED IS:

1. A method of manufacturing a laterally diffused metal oxide semiconductor (LDMOS) device, comprising:

forming a lightly-doped source/drain region with a first dopant, the lightly-doped source/drain region located between first and second isolation structures; and

creating a gate over the lightly-doped source/drain region.

2. The method as recited in Claim 1 wherein forming includes forming a lightly-doped source/drain region with a first N-type dopant.

3. The method as recited in Claim 2 wherein the first N-type dopant has an implant dose ranging from about 1E12 atoms/cm^2 to about 1E13 atoms/cm^2.

4. The method as recited in Claim 3 wherein the first N-type dopant has an implant dose of about 5E12 atoms/cm^2.

5. The method as recited in Claim 1 further including diffusing a second dopant at least partially across the lightly-

doped source/drain region and under the gate to form a first portion of a channel.

6. The method as recited in Claim 5 wherein diffusing the second dopant includes diffusing a second P-type dopant having an implant dose ranging from about 1E13 atoms/cm^2 to about 1E14 atoms/cm^2.

7. The method as recited in Claim 5 wherein diffusing the second dopant includes diffusing a second P-type dopant having an implant dose about 100 times higher than an implant dose of the first dopant.

8. The method as recited in Claim 5 further including placing a heavy concentration of the first dopant in a region adjacent a source side of the gate, and in the lightly-doped source/drain region adjacent a drain side of the gate.

9. The method as recited in Claim 8 wherein placing includes placing the heavy concentration of the first dopant in the lightly-doped source/drain region a distance ranging from about 2000 nm to about 3000 nm from the drain side of the gate.

10. The method as recited in Claim 8 wherein placing includes placing an implant dose of the first dopant ranging from about 1E15 atoms/cm^2 to about 1E16 atoms/cm^2.

11. A method of manufacturing an integrated circuit, comprising:

fabricating laterally diffused metal oxide semiconductor (LDMOS) transistors, including:

forming a lightly-doped source/drain region with a first dopant, the lightly-doped source/drain region located between first and second isolation structures; and

creating a gate over the lightly-doped source/drain region;

depositing interlevel dielectric layers over the LDMOS transistors; and

creating interconnect structures in the interlevel dielectric layers and interconnecting the LDMOS transistors to form an operative-integrated circuit.

12. The method as recited in Claim 11 wherein forming includes forming a lightly-doped source/drain region with a first N-type dopant.

13. The method as recited in Claim 12 wherein the first N-type dopant has an implant dose ranging from about 1E12 atoms/cm^2 to about 1E13 atoms/cm^2.

14. The method as recited in Claim 13 wherein the first N-type dopant has an implant dose of about 5E12 atoms/cm^2.

15. The method as recited in Claim 11 further including diffusing a second dopant at least partially across the lightly-doped source/drain region and under the gate to form a first portion of a channel.

16. The method as recited in Claim 15 wherein diffusing the second dopant includes diffusing a second P-type dopant having an implant dose ranging from about 1E13 atoms/cm^2 to about 1E14 atoms/cm^2.

17. The method as recited in Claim 15 wherein diffusing the second dopant includes diffusing a second P-type having an implant dose about 100 times higher than an implant dose of the first dopant.

18. The method as recited in Claim 15 further including placing a heavy concentration of the first dopant in a region adjacent a source side of the gate, and in the lightly-doped source/drain region adjacent a drain side of the gate.

19. The method as recited in Claim 18 wherein placing includes placing the heavy concentration of the first dopant in the lightly-doped source/drain region a distance ranging from about 2000 nm to about 3000 nm from the drain side of the gate.

20. The method as recited in Claim 18 wherein placing includes placing an implant dose of the first dopant ranging from about 1E15 atoms/cm^2 to about 1E16 atoms/cm^2.